NSN 5961-01-349-9922

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-349-9922 **Inclosure Material:** Metal **Overall Length:** Between 0.250 inches and 0.310 inches **Terminal Length:** Between 0.200 inches and 0.225 inches **Overall Height:** Between 0.400 inches and 0.600 inches **Overall Width:** Between 1.800 inches and 2.700 inches **Function For Which Designed:** Microwave **Mounting Method: Terminal Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 4.0 breakdown voltage, dc **Current Rating Per Characteristic:** 10.00 microamperes forward current, average peak **Power Rating Per Characteristic:** 1.0 watts small-signal input power, common-collector major **Capacitance Rating In Picofarads:** 0.15 **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius ambient air **Special Features:** Beam lead schottky diode for detectors; junction pattern arrangement: pn **Precious Material And Location:** Terminals gold **Precious Material: Terminal Type And Quantity:** 2 beam lead Shelf Life: N/a **Unit Of Measure: Demilitarization:**

No

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